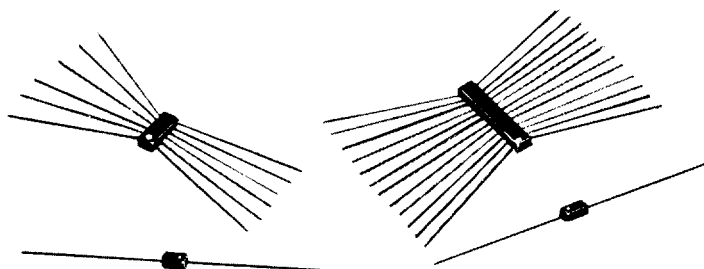


NIGHT VISION

H.V. RECTIFIER DIODES & ARRAYS



These diodes and arrays have been specifically designed for use in night vision and image intensifier equipment power supplies. They offer unusual characteristics that have not been previously available. As a result of a proprietary EDI diffusion process, they feature small size and a unique combination of extremely low leakage and ultra fast recovery time.

Diode Specifications @ 23°C (Absolute Maximum Unless Otherwise Specified)	NVDX Diode (Standard Recovery)	NVD Diode And Diode Arrays (Fast Recovery)
PRV	1,000 Vdc	1,200 Vdc
I_F	5.0mA	5.0mA
V_F @ 1 mA dc	6.0 V	4.0 V
Junction Capacitance	_____	0.35 pF. @ 500 Vdc
I_R @ 1,000 Vdc @ 23°C	0.5 nanoamperes	_____
I_R @ 1,000 Vdc @ 55°C	5.0 nanoamperes	_____
I_R @ 500 Vdc	_____	1.0 nanoamperes typical 5.0 nanoamperes max.
I_R @ 500 Vdc @ 55°C	_____	25 nanoamperes
I_R @ 250 Vdc @ 23°C	0.1 nanoamperes typical 0.25 nanoamperes max.	_____
I_R @ 250 Vdc @ 55°C	1.0 nanoamperes typical 2.0 nanoamperes max.	_____
T_{rr} (Reverse Recovery Time), Fig. 4	_____	50 ns typical 100 ns max.
Temperature Range: Operating	- 55 °C to + 100 °C	- 55 °C to + 100 °C
Temperature Range: Storage	- 63 °C to + 125 °C	- 63 °C to + 125 °



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Figure 1 NVDX

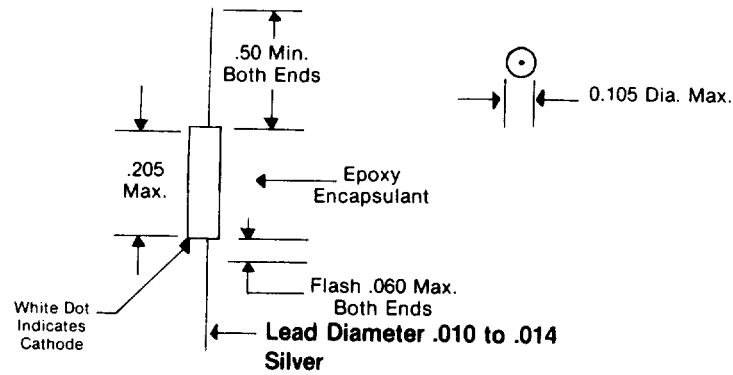


Figure 2 NVD

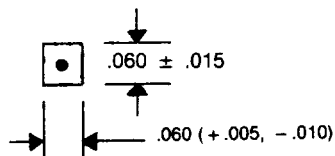
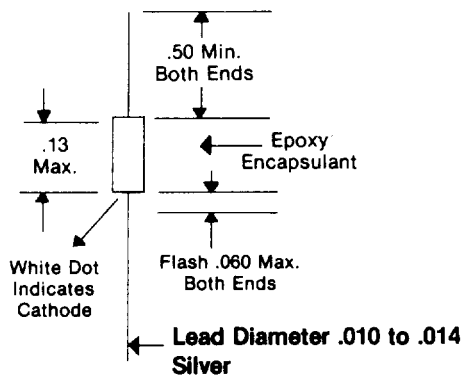
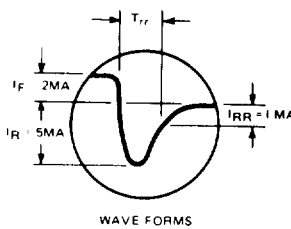


Figure 4

REVERSE RECOVERY TEST METHOD

RECOVERY WAVE FORM



RECOVERY TEST CIRCUIT

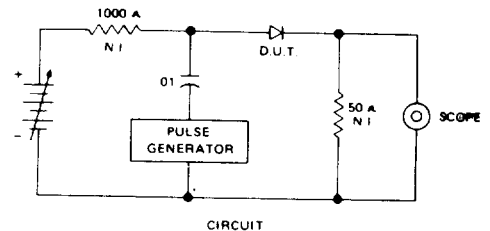


Figure 3 NVD ARRAYS

PART NO.	NO. OF DIODES	DIM "L"
NVD - 1	1	SEE FIG. 2
NVD - 2	2	.100 MAX
NVD - 4	4	.200 MAX
NVD - 6	6	.275 MAX
NVD - 8	8	.360 MAX
NVD - 12	12	.515 MAX

